

P-Channel Enhancement Mode Field Effect Transistor

NDT2955

General Description

This 60 V P-Channel MOSFET is produced using onsemi's high voltage Trench process. It has been optimized for power management applications.

Features

- -2.5 A, -60 V
 - ◆ $R_{DS(ON)} = 300\text{ m}\Omega$ @ $V_{GS} = -10\text{ V}$
 - ◆ $R_{DS(ON)} = 500\text{ m}\Omega$ @ $V_{GS} = -4.5\text{ V}$
- High Density Cell Design for Extremely Low $R_{DS(ON)}$.
- High Power and Current Handling Capability in a Widely Used Surface Mount Package
- This is a Pb-Free Device

Applications

- DC/DC Converter
- Power Management

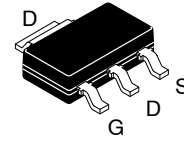
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-Source Voltage	-60	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current	- Continuous (Note 1a)	A
		- Pulsed	
P_D	Maximum Power Dissipation (Note 1a)	3.0	W
		(Note 1b)	
		(Note 1c)	
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

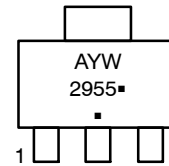
THERMAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	42	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	12	$^\circ\text{C/W}$



SOT-223
CASE 318H-01

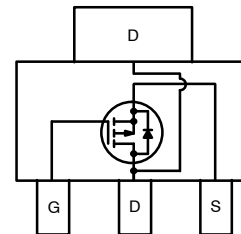
MARKING DIAGRAM



A	= Assembly Location
Y	= Year
W	= Work Week
2955	= Specific Device Code
■	= Pb-Free Package

(Note: Microdot may be in either location)

PINOUT DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping [†]
NDT2955	SOT-223 (Pb-Free)	4000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](http://www.onsemi.com/BRD8011/D).

NDT2955

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
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AVALANCHE RATINGS

W _{DSS}	Drain-Source Avalanche Energy	Single Pulse, V _{DD} = 30 V, I _D = 2.5 A	–	–	174	mJ
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OFF CHARACTERISTICS

BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = –250 μA	–60	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = –250 μA, Referenced to 25°C	–	–60	–	mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = –60 V, V _{GS} = 0 V	–	–	–10	μA
I _{GSSF}	Gate-Body Leakage, Forward	V _{GS} = –20 V, V _{DS} = 0 V	–	–	100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	V _{GS} = –20 V, V _{DS} = 0 V	–	–	–100	nA

ON CHARACTERISTICS (Note 2)

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = –250 μA	–2	–2.6	–4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _D = –250 μA, Referenced to 25°C	–	5.7	–	mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = –10 V, I _D = –2.5 A	–	95	300	mΩ
		V _{GS} = –4.5 V, I _D = –2 A	–	163	500	
		V _{GS} = –10 V, I _D = –2.5 A, T _J = 125°C	–	153	513	
I _{D(on)}	On-State Drain Current	V _{GS} = –10 V, V _{DS} = –5 V	–12	–	–	A
g _{FS}	Forward Transconductance	V _{DS} = –10 V, I _D = –2.5 A	–	5.5	–	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = –30 V, V _{GS} = 0 V, f = 1.0 MHz	–	601	–	pF
C _{oss}	Output Capacitance		–	85	–	pF
C _{rss}	Reverse Transfer Capacitance		–	35	–	pF

SWITCHING CHARACTERISTICS (Note 2)

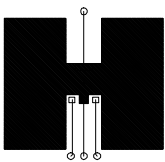
t _{d(on)}	Turn – On Delay Time	V _{DD} = –30 V, I _D = –1 A, V _{GS} = –10 V, R _{GEN} = 6 Ω	–	12	21	ns
t _r	Turn – On Rise Time		–	10	20	ns
t _{d(off)}	Turn – Off Delay Time		–	19	34	ns
t _f	Turn – Off Fall Time		–	6	12	ns
Q _g	Total Gate Charge	V _{DS} = –30 V, I _D = –2.5 A, V _{GS} = –10 V	–	11	15	nC
Q _{gs}	Gate-Source Charge		–	2.4	–	nC
Q _{gd}	Gate-Drain Charge		–	2.7	–	nC

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I _S	Maximum Continuous Drain–Source Diode Forward Current		–	–	–2.5	A
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = –2.5 A (Note 2)	–	–0.8	–1.2	V
t _{rr}	Diode Reverse Recovery Time	I _F = –2.5 A, dI _F /d _t = 100 A/μs	–	25	–	ns
Q _{rr}	Diode Reverse Recovery Charge		–	40	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

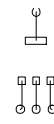
1. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design.



a. 42°C/W when mounted on a 1 in² pad of 2 oz copper.



b. 95°C/W when mounted on a 0.066 in² pad of 2 oz copper.



c. 110°C/W when mounted on a minimum pad.

2. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%.

TYPICAL CHARACTERISTICS

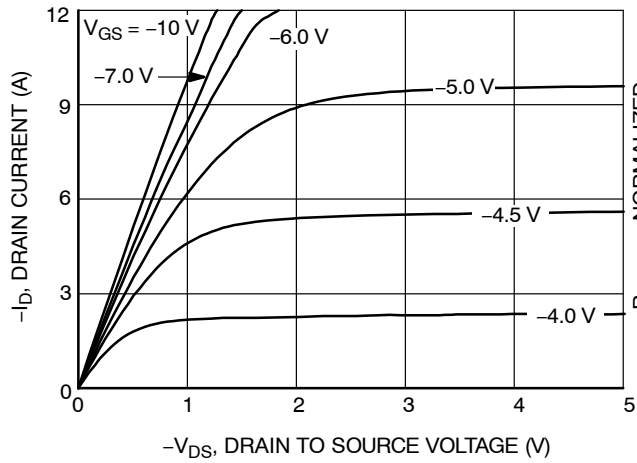


Figure 1. On-Region Characteristics

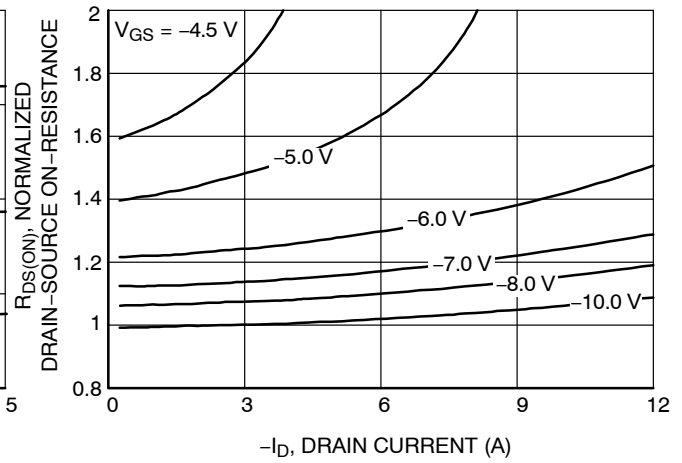


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

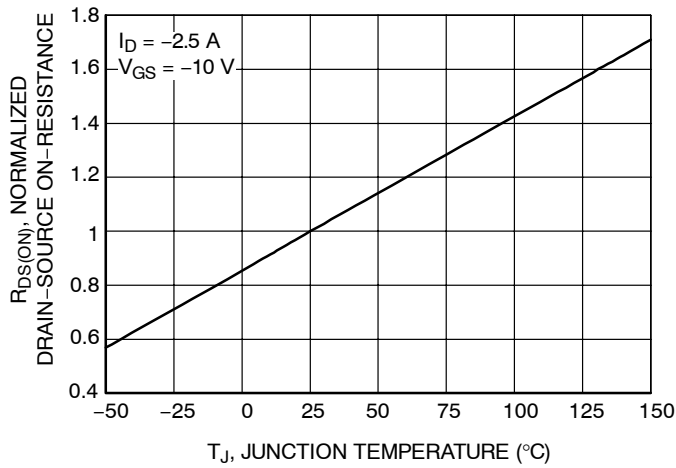


Figure 3. On-Resistance Variation with Temperature

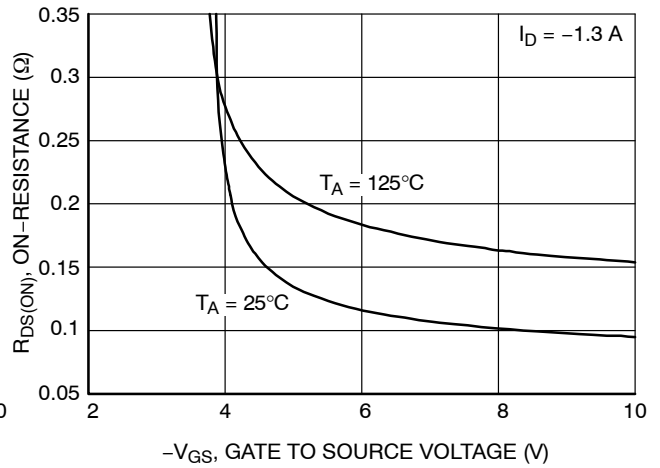


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

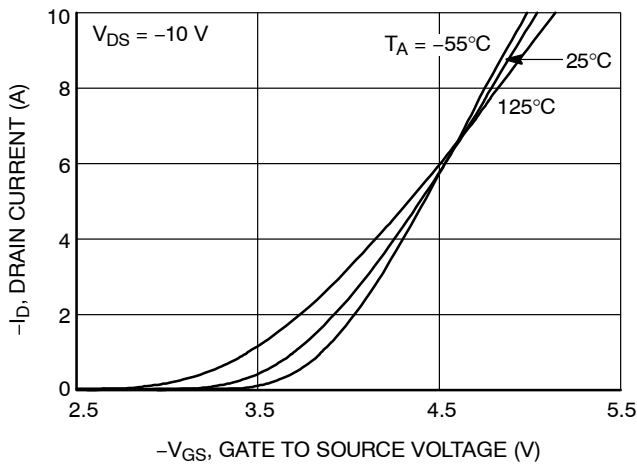


Figure 5. Transfer Characteristics

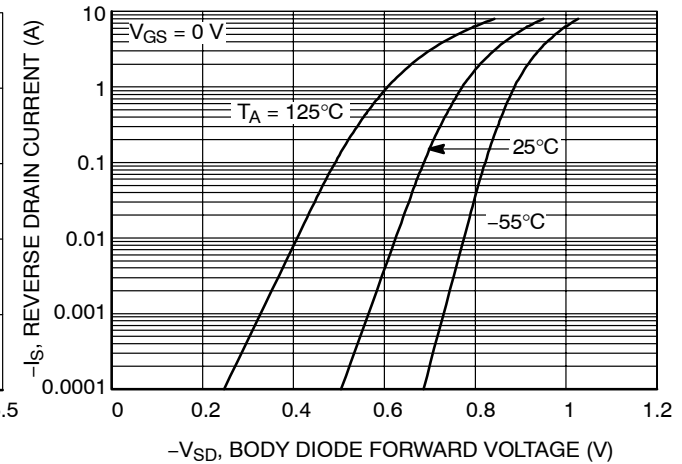
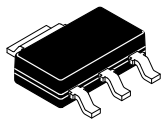
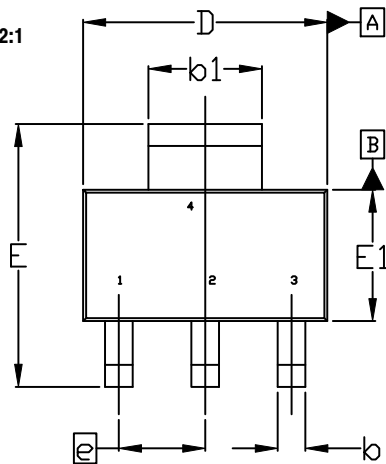


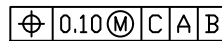
Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature



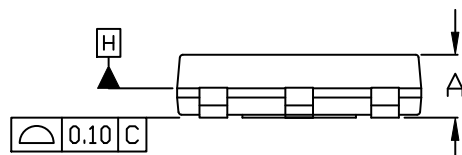
SCALE 2:1



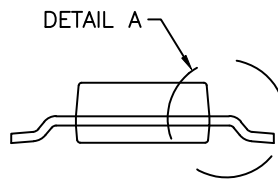
TOP VIEW



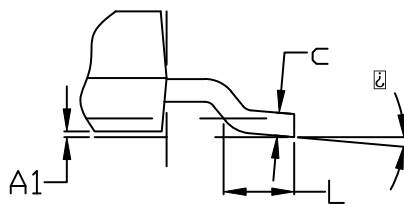
NOTE 7



SIDE VIEW

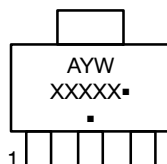


END VIEW



DETAIL A

GENERIC MARKING DIAGRAM*



A = Assembly Location
Y = Year
W = Work Week
XXXXX = Specific Device Code
▪ = Pb-Free Package

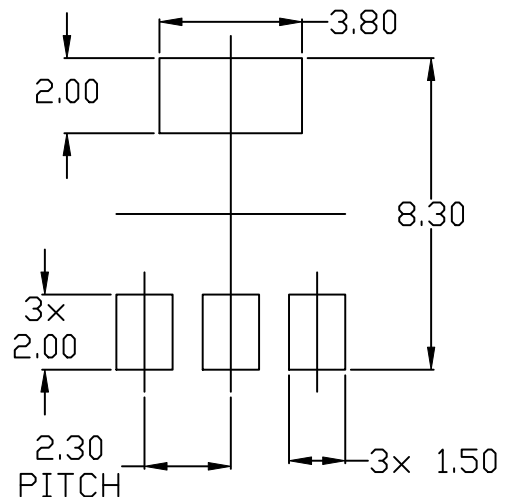
(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E1 ARE DETERMINED AT DATUM H. DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. SHALL NOT EXCEED 0.23mm PER SIDE.
4. LEAD DIMENSIONS b AND b1 DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION IS 0.08mm PER SIDE.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
7. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.80
A1	0.02	0.06	0.11
b	0.60	0.74	0.88
b1	2.90	3.00	3.10
c	0.24	---	0.35
D	6.30	6.50	6.70
E	6.70	7.00	7.30
E1	3.30	3.50	3.70
e	2.30 BSC		
L	0.25	---	---
⌀	0°	---	10°



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

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